#### WELCOME FROM RANDY WOLFF, IBIS OPEN FORUM

Ladies and Gentlemen,

As chair of the IBIS Open Forum it is my pleasure to welcome you to the 2019 Asian IBIS Summit in Shanghai and to thank you for your presentations and participation. We are grateful to our sponsors Huawei Technologies, ANSYS, Cadence Design Systems, Keysight Technologies, Synopsys, and ZTE Corporation, for making this event possible.

Since 1993, IBIS has provided the digital electronics industry with specifications to make signal, timing, and power integrity analyses much easier and faster. With the introduction of IBIS-AMI in 2008, the IBIS community generated new energy for high speed electronic design. IBIS is now known by engineers worldwide and is a required technology for many applications. IBIS Version 7.0 was released in 2019, adding enhancements for IBIS-AMI and supporting advanced interconnect modeling.

Support for IBIS in Asia has been strong, and the IBIS Open Forum looks forward to continued innovation and contributions from technology companies in Asia.

Thank you!

Jun U. W.M

Randy Wolff Micron Technology Chair, IBIS Open Forum

#### WELCOME FROM RANDY WOLFF, IBIS OPEN FORUM

女士们先生们,

作为 IBIS 开放论坛的主席,我高兴地欢迎您参加 2019 年上海亚洲 IBIS 峰 会,感谢您的介绍和参与。我们非常感谢我们的赞助商华为技术有限公司,ANSYS, Cadence Design Systems, Keysight Technologies, Synopsys,为此事件做出了可能。

自 1993 年以来, IBIS 为数字电子行业提供了使信号,时序和电源完整性分析更容易和更快速的规范。随着 IBIS-AMI 在 2008 年的推出, IBIS 社区为高速电子设计创造了新的能量。 IBIS 现在已被世界各地的工程师所了解,是许多应用所需的技术。2019 年,新的 IBIS 7.0 版本包含了更多的 IBIS-AMI 模型和互联接口模型的定义及提升。

IBIS 在亚洲的支持一直很强, IBIS 开放论坛期待着亚洲技术公司的不断创新和贡献。

谢谢!

Phant II. With

Randy Wolff (**兰迪·沃尔夫**) Micron Technology 公司 主席, IBIS 开放论坛

#### WELCOME FROM HANG YAN, HUAWEI TECHNOLOGIES

Ladies and Gentlemen,

On behalf of Huawei Technologies, welcome to the 15th annual Asian IBIS Summit (China). I would like to express my appreciation to IBIS Open Forum and all the sponsors for co-organizing this event.

Since 2005, IBIS Asian Summit in China has been the top-level international conference in high speed digital design society in China. I am looking forward to working with IBIS members in China, and to expand our participation in the region. With the demands of high speed design, modeling and simulation technology will still be the key to find the solution. Accuracy, efficiency and complexity are the challenge we are facing now. Intelligence and digitization will be the trend.

Huawei has been actively involved in all IBIS society's events. We hope to resolve high speed link issues with IBIS Open Forum, EDA vendors and IC vendors. Your comments and suggestions will be deeply appreciated! And any suggestion for China region technical discussion and activity are also welcome!

Welcome all of you to Shanghai! Hope you will enjoy all the technical discussions and sharing throughout the meeting, and have a nice journey!

Thank you! Hang Yan Huawei Technologies

#### WELCOME FROM HANG YAN, HUAWEI TECHNOLOGIES

各位专家,各位来宾:

我代表华为公司, 欢迎大家来参加第 15 洲 IBIS 技术研讨会, 衷心地感谢 IBIS 协会组织本次会议。

自从 2005 年以来, IBIS 技术研讨会已经成为了中国高速设计领域的一次盛会。我很高兴有机会与 IBIS 协会一起促进和扩大在该领域的分享。在未来的高速设计中,模型和仿真技术仍将是解决问题的重要手段,准确度、速度和复杂度是我们面临的挑战,智能化和数字化是未来的方向。

华为积极参与各项 IBIS 活动,希望与 IBIS 协会、EDA 软件、芯片公司一道 来共同解决许多高速链路设计上的挑战,欢迎大家会上讨论。同时也欢迎大 家对我们中国区在 IBIS 技术讨论和组织上提出建议。

欢迎 IBIS 专家来到上海,希望你们能够喜欢所有的技术讨论和会议分享, 度过美好一天。

谢谢大家 华为公司 严航

### AGENDA AND ORDER OF THE PRESENTATIONS

### (The actual agenda might be modified)

	IBIS SUMMIT MEETING AGENDA
9:00	SIGN IN - Vendor Tables Open at 8:30
9:30	<pre>WELCOME - Yan, Hang (Paul)  (Huawei Technologies, China) - Wolff, Randy (Chair, IBIS Open Forum)  (Micron Technology, USA)</pre>
9:40	<pre>IBIS Chair's Report</pre>
10:00	How to Obtain Buffer Impedance from IBIS
10:20	C-PHY SI Simulation with IBIS Model
10:35	BREAK (Refreshments and Vendor Tables)
10 <b>:</b> 55	Innovations in DDR Memory Simulation
11:20	<pre>IBIS-AMI &amp; COM Co-design for 25G Serdes</pre>
12:00	FREE BUFFET LUNCH (Hosted by Sponsors) - Vendor Tables

#### AGENDA AND ORDER OF THE PRESENTATIONS (Continued)

- 13:30 How To Fix a Short Channel Problem With AMI and COM Simulation . . . 55 Ye, Dongdong; Zhu Shunlin (ZTE Corporation, China) [Presented by Ye, Dongdong (ZTE Corporation, China)]

- 15:05 CONCLUDING ITEMS
- 15:10 END OF IBIS SUMMIT MEETING
- 15:10 **BREAK** (Refreshments and Vendor Tables))
- 15:30 VENDOR PRESENTATIONS, MODERATOR
   Wang, Lance (Vice-chair, IBIS Open Forum)
   (Zuken, USA)
- 17:30 END OF VENDOR PRESENTATIONS

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Organization		
	Task Groups	
<ul> <li>Interconnect Task         <ul> <li>Chair: Michael Mi</li> <li><u>http://ibis.org/int</u></li> <li>Develop on-die/p</li> </ul> </li> </ul>	Group rmak, Intel <u>erconn_wip/</u> ackage/module/connector interconnect modeling BIRDs	
<ul> <li>Advanced Technol         <ul> <li>Chair: Arpad Mur</li> <li><u>http://ibis.org/atr</u></li> <li>Develop most oth</li> </ul> </li> </ul>	ogy Modeling Task Group anyi, Mentor, A Siemens Business <u>mwip/</u> er technical BIRDs	
<ul> <li>Quality Task Grou         <ul> <li>Chair: Mike LaBor</li> <li><u>http://ibis.org/qu</u></li> <li>Oversee IBISCHK</li> </ul> </li> </ul>	p nte, SiSoft (MathWorks) <u>ality_wip/</u> parser testing and development	
<ul> <li>Editorial Task Grou</li> <li>Chair: Michael Mi</li> <li><u>http://ibis.org/ed</u></li> <li>Produce IBIS Spece</li> </ul>	JP rmak, Intel itorial_wip/ ification documents	
	BIRD = Buffer Issue Resolution Document 2019 Asian IBIS Summits - IBIS Chair's Report	6

















BIRD Template Link on the BIRD
Webpage

ID#	Issue Title	Requester	Date Submitted	Date Accepted	Supporting Version
200	C_comp Model Using IBIS-ISS or Touchstone	Randy Wolff, Micron Technology, Inc. Walter Katz, Signal Integrity Software, Inc.	July 9, 2019	September 27, 2019	
199	Fix Rx_Receiver_Sensitivity Inconsistencies	Arpad Muranyi, Mentor a Siemens Business	March 19, 2019	June 7, 2019	
198	Keyword additions for On Die PDN (Power Distribution Network) Modeling	Kanaki Murata, Reob Co., Ltd.; Mnyoko Goto; Ricoh Co., Ltd.; Kazuyuki Salanta; Renesas Electronics Corporation; Kazunori Yamada; Renesas Electronics Corporation; Kouji Ichikawa; Denso Corporation; Atsushi Tomisham; Toshiba Electronic Devices & Storage Corporation; Takashi Hasegava; Sony LSI Design Inc.; Koichi Seko, Panasonic Industrial Devices Systems and Technology Co., Ltd.; Toshika Kanamote, Hirosaki Liniversityi Megumi Ono; Socionext Inc.	March 11, 2019		
197.4	New AMI Reserved Parameters DC_Offset and NRZ_Threshold	Walter Katz, SiSoft, Ambrish Varma, Cadence Design Systems, Randy Wolff, Micron Technology, Justin Butterfield, Micron Technology, Fangyi Rao, Keysight Technologies	November 27, 2018, December 4, 2018, January 15, 2019, June 25, 2019, July 23, 2019		
196.1	Prohibit Periods at the End of File Names	Arpad Muranyi, Mentor Graphics, A Siemens Business	September 25, 2018, October 12, 2018	October 12, 2018	7.0
195.1	Enabling [Rgnd] and [Rpower] Keywords for Input Models	Michael Mirmak, Intel Corp.	June 19, 2018, June 29, 2018	August 31, 2018	
		2019 Asian IBIS Summits - IBIS Chair's Report		1	15











#### Impedance Concept

- The impedance of a two-terminal circuit element is represented as a complex quantity Z. The polar form conveniently captures both magnitude and phase characteristics as Z = |Z|e<sup>j arg(Z)</sup>
- where the magnitude |Z| represents the ratio of the voltage difference amplitude to the current amplitude, while the argument arg(Z) (commonly given the symbol  $\theta$  gives the phase difference between voltage and current). *j* is the imaginary unit and is used instead of *i* in this context to avoid confusion with the symbol for electric current.
- In Cartesian form, impedance is defined as Z = R + jX
- where the real part of impedance is the resistance R and the imaginary part is the reactance X.



ZUKEN

to minimum for the reactance X. So, in this case, the resistance R is the main factor for impedance matching.





























Bailing Zhang **张百玲** ANSYS

Asian IBIS Summit Shanghai, PRC November 1, 2019

## Outline

≻C-PHY interface instruction

 $\succ {\rm How}$  to use IBIS model to do the C-PHY SI simulation

≻Check the simulation result

≻Summary







## Summary

Use IBIS model to do the C-PHY SI simulation is very convenient, accurate and fast.

From the simulation we can best evaluate the quality of C-PHY signal and make the product successful.













# **Change, Challenges and Solutions**

- 1. Crosstalk, Jitter and Bit-Error-Rate (BER) Specs
- 2. Closed eyes need equalization and training
- 3. Innovations in Simulation and Modeling of DDR5 & LPDDR5 systems


























# Introducing IBIS AMI for DDR Signals EQ Necessary for TX: 3 Tap Pre-Emphasis (Feed Forward Equalization)

- EQ Necessary for RX: CTLE/VGA/DFE
- IBIS-AMI offers
  - > Portability One IBIS-AMI mode can run on many EDA tools
  - > IP Protection Digital signal processing behavior is concealed in model DLL/shared object
  - ➢ Interoperability IC Vendor A ←→IC Vendor B (AMI defines a common interface between the vendor model and the EDA channel simulator)
  - > Non-linearity As complex as the model vendor wishes the model to be
  - > Performance Ultra low BER simulations in seconds not days over the traditional SPICE simulation
- AMI has been widely adopted by IC, system and EDA companies for SerDes signals but this is the first application to DDR single-ended signals.











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# IBIS-AMI & COM Co-design for 25G Serdes

# Asian IBIS Summit Shanghai, PRC November 1, 2019

Nan Hou, Amy Zhang, Guohua Wang, David Zhang, Anders Ekholm

# AGENDA

- Traditional IBIS-AMI
- COM Overview
- IBIS-AMI Co-design with COM for 25G
- Two example channels
- Co-simulation Conclusion
- Next Steps





















3

# 25G CO-SIMULATION PROCESS

- Extraction of passive S parameter model of the simulation channel
- Use S parameter to do COM simulation
- IBIS simulation using COM recommended EQ parameter
- IBIS simulation to sweep EQ parameter
- Comparing the eye diagram in time domain

# Page 13 (29)

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# CO-SIMULATION CONCLUSION

- COM enables passive channel evaluation of high-speed signals at early design phase
- COM recommended EQ parameters are suitable for same channel in time domain simulation
- COM simulation is faster, making them more suitable for the post-layout phase of large designs to sweep EQ parameters

Page 26 (29)



# NEXT STEPS Model crosstalk in actual link Co-simulation for 56G PAM-4 Accuracy of IBIS-AMI model Correlation of Co-simulation with measurement

Page 28 (29)





















### AMI and COM Simulation **AMI Simulation Result** AMI result eye height(V) Inconsistent with the trend of actual 0.06 Minimun eye width(ps) 0.055 6.6 6.4 6.2 5.8 5.6 5.4 5.2 test results 0.05 0.045 The eye width and height decrease 0.04 with the increase of channel length, Minimum 0.035 0.03 leading to a decay in system margin Backplane line length(inch) Minimun eye width /inimum eye height 🛛 🗕 COM Simulation Result Consistent with the trend of actual COM result 7.2 test results 7 > COM value increases with the on 6.8 6.6 Alue increase of backplane line length at 6.4 0 6.2 first. After peaking, COM value then starts to decrease while the backplane line length continues to <sup>12</sup> 3ປາ<sup>2</sup> 4ປາ<sup>6</sup> ແ<sup>12</sup> 3ປາ<sup>3</sup> 4ປາ<sup>8</sup> 4ປ<sup>4</sup> 4ປ<sup>4</sup> 6 (M<sup>4</sup>) 4</sub>ປະ Backplane line length(inch) increase



## AMI and COM Simulation

**AMI Simulation Result** 

- Trends become similar to COM results.
- The eye width and height increase with the loss increases at first
- The eye width and height then starts to decrease while the loss continues to increase

**COM Simulation Result** 

- Consistent with the trend of actual test results
- COM value increase as loss increases at first
- After peaking, COM value then start to decrease while loss continues to increase



## AMI and COM Simulation

Why do such rules appear?

COM simulation can provide more information compared to AMI simulation COM simulation tool supports to export insertion loss curve after CTLE

- For short channel, the compensation in insertion loss is too much at low frequency
- With the increase of channel length, the compensation in insertion loss at high and low frequency tends to balance



# AMI and COM Simulation

The comparison of the influence of CTLE on channel is shown in the following table

- > For short channel, CTLE has little influence on ISI
- > For long channel, CTLE has a great influence on ISI
- When CTLE is operating, the proportion of ISI in short channel is greater than that of long channel

When the channel insertion loss is very small, CTLE compensates too much for the insertion loss at low frequency band, which is not conducive to reducing ISI

Length of line in Backplane	CTLE	СОМ12ММ	FOM	ASV	seg_ISI	ISI/ASV
1in	off	6.2315	17.4946	35.9423	0.0028494	7.93%
1111	on	6.5206	17.7784	35.8026	0.0025736	7.19%
10in	off	4.8362	16.1031	15.4962	0.0016943	10.93%
10111	on	6.4419	17.6499	10.9379	0.00065234	5.96%



# Summary

- When the channel insertion loss is very small, CTLE compensates too much for the insertion loss at low frequency band, which is not conducive to reducing ISI
- In high-speed design, the length of the channel should be designed meeting the requirements of a certain value
- During AMI simulation, it will be more helpful to find problem if more detailed information can be output (such as CTLE curve).
- When analyzing problems, it is recommended that both COM and AMI simulation should be done if possible.





# Agenda

Think Bigger. Reach Further.

- 112G Passive Channel Modeling: C2M and CR loopback.
- COM Simulation for 100G-CR loopback channel.
- Conclusion











		Think Bigger. Reach Further.
	100G-CR COM Simulation	
8		



802.3ck_COM Simulation F	Results_100G-CR	2M OSFP Loopback	Think Bigger. Reach Further.
Iestcase 2 results Iestcase 2 results code_revision: '2.60' 211est: 95.6632 222est: 95.6721 ERLII: 15.7669 ERL22: 15.7137 ERL2: 15.7137 RVFFE; '' RVFFEgain: '' config_file: 'F:\1125 Data file_names: 'RR_eval levels: 4 Pkg_len_REX1: [29.18000 0 Pkg_len_REX1: [29.18000 0 Pkg_len_REX1: [29.18000 0 Rd_iepad: [45 45] pkg_Z_c: [2x4 double] C_v: [0 0] bud_rate_(EH: 53.1250 f_Nyquist_GH: 26.5625 BER: 1.0000-04 FOM: 13.7052 signa_H: 3.5284e-04 DFE4_RS5: 0.3860 channel_operating_margin_GB: 2.3381 available_signal_after_eq_NY: 3.1441 pressioned pressioned contained pressioned pres	\IBIS Subnit\112_COM(nellitz_ 1126_CR_COM_VICID, KR_eval_ 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	SIR_ISLATE, FEXT SIR_ICX, FXX, NEXT, FEXT SIR_ICX, SIX, SIX, SIX, SIX, SIX, SIX, SIX, SI	<pre>: 2.4021 : 1.6790 : 1.2011 : 0.3229 : 1.1099 : 0.8709 : 0.8709 : 0.8709 : 0.8709 : 0.8709 : 0.8709 : 0.8709 : 0.8709 : 0.2984 : 0.8877 : 32.0779 : 0.4236 : (2.1250e+10 5.3125e+10 2.1250e+10) : (2.141 double) : (2.141 double) : (2.150e+10 4 : 0.2335=-04 : 4.2643e-04 : 0.3335=-04 : 4.2643e-04 : 3.3051=-04 : 4.2643e-04 : 3.3051=-04 : 4.2643e-04 : 3.3051=-04 : 4.2643e-04 : 5.5214e-04 : 5.</pre>
uneq_FIR_peak_time: 1.5612e-08 steady_state_voltage_nV: 29.1113 10 FOM_LLD: 0.3399		sgm_IX total_IL_wpkgs_dB_at_Fnq IL_dB_channel_only_at_Fnq	: 2.2228e-04 : 39.1631 : 27.1907





		<u>_:</u> _			1000			lassbaa	Think Bigger. Re	
2.30		Sin	nulation	1 Results	_1000	a-CH		Looppac	K	
nfig_file	s:									
0==	Table 93A-1 parame	eters		I/0	control			Table 93A? parame	ters	
Parameter	Setting	Units	Information	DIAGNOSTICS	1	logical	Parameter	Setting	Units	
f_b	53.125	GBd		DISPLAY_WINDOW	1	logical	package ti gamma0 a1 a2	[0 0.0009909 0.0002772]		
f min	0.05	GHz		CSV REPORT	1	logical	package tI tau	6.141E-03	ns/mm	
Delta f	0.01	GHz		RESULT DIR	\results\100GEL	KR {date}	package Z c	[87.5 87.5 ; 92.5 92.5 ]	Ohm	
Cd	[1.2e-4 1.2e-4]	nF	[TX RX]	SAVE FIGURES	1	logical				
Ls	[0.12, 0.12]	nH	[TX RX]	Port Order	[1324]			Table 92?2 parameters 5.2dB at 26.56GHz		
Cb	[0.3e-4 0.3e-4]	nF	[TX RX]	RUNTAG	KR eval		Parameter	Setting		
z p select	[12]		[test cases to run]	COM CONTRIBUTION	0	logical	board tl gamma0 a1 a2	[0 0.000599 0.0001022]	1.286 dB/in or 0.0506 dB/mm at 100 ohms	
z_p (TX)	[12 31; 1.8 1.8]	mm	[test cases]	Ope	rational		board tI tau	6.200E-03	ns/mm	
z_p (NEXT)	[12 29; 1.8 1.8]	mm	[test cases]	COM Pass threshold	3	dB	board_Z_c	90	Ohm	
z_p (FEXT)	[12 31; 1.8 1.8]	mm	[test cases]	ERL Pass threshold	10	dB	z_bp (TX)	102.7	mm	
z p (RX)	[12 29; 1.8 1.8]	mm	[test cases]	DER 0	1.00E-04		z bp (NEXT)	102.7	mm	
Ср	[0.87e-4 0.87e-4]	nF	[TX RX]	T.r.	6.16E-03	ns	z_bp (FEXT)	102.7	mm	
R_0	50	Ohm		FORCE_TR	1	logical	z_bp (RX)	102.7	mm	
R_d	[ 45 45]	Ohm	[TX RX]	Include PCB	0	logical				
A_v	0.39	V	vp/vf=.694	TDR and	ERL options					
A_fe	0.39	V	vp/vf=.694	TDR	1	logical		Floating Tap Cont	rol	
A_ne	0.578	V		ERL	1	logical	N_bg	0	012 or 3 groups	
L	4			ERL_ONLY	0	logical	N_bf	0	taps per group	
M	32			TR_TDR	0.01	ns	N_f	40	UI span for floating taps	
	filter and Eq			N	3000		bmaxg	0.1	max DFE value for floating taps	
f.r.	0.75	*fb		beta_x	2.53E+09					
c(0)	0.5		min	rho_x	0.25					
c(-1)	[-0.3:0.02:0]		[min:step:max]	fixture delay time	0	s				
c(-2)	[0:0.02:0.12]		[min:step:max]	TDR_W_TXPKG	0					
c(-3)	[-0.06:0.02: 0]		[min:step:max]	N_bx	24	UI	yellow indicates WIP			
c(1)	[-0.2:0.05:0]		[min:step:max]	Receiv	ver testing					
N_b	24	UI		RX_CALIBRATION	0	logical				
b_max(1)	0.85			Sigma BBN step	5.00E-03	V				
b_max(2N_b)	0.3			Noi	se, jitter					
g_DC	[-20:1:0]	dB	[min:step:max]	sigma_RJ	0.01	UI				
f_z	21.25	GHz		A_DD	0.02	UI				
f_p1	21.25	GHz		eta_0	8.20E-09	V^2/GHz				
f_p2	53.125	GHz		SNR_TX	33	dB				
g DC HP	[-6:1:0]		[min:step:max]	R LM	0.95					
f µp p7	0.6640635	CHA								

# Conclusion

• In the early stage of 112G product development, Celestica is preparing the channel modeling for IBIS-AMI simulation. Most 112G IBIS-AMI model will be available in 2020-Q1.

Think Bigger. Reach Further.

- PCB still can be an option for 112G switch, but the SI performance of the PCB need to be improved (M8 Level).
- In our simulation, the host channel trace length is only 6inch, it's difficult to improve the insertion loss performance to get better COM margin, so it has a higher expectation on Xtalk to improve the SNR (BER).
- Will continue update the 112G simulation.





# Two Concerns:

- As the transmission rate of memory bus goes beyond 5Gbps, besides the wellknown timing and overshoot/undershoot analysis, it requires BER prediction analysis and channel analysis
- Two additional concerns we need to face while using channel engine to deal with memory bus:
  - Asymmetric rising/falling edges

Different from differential serial buses, single-ended memory buses will have non-symmetrical rising and falling edges due to the inherent difference between these two kinds of circuits

- Strobes as timing reference

While the sampling clock ticks in serial bus are recovered from the signal itself by CDR, the sampling clocks or the timing references in memory bus will be the strobes rather than any recoveries

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## Overview

- As channel simulation and IBIS-AMI modeling methods are adapted from serial link to DDR interface analysis, we encounter IBIS I/O models with asymmetric rising and falling edges
- This is different from the highly symmetric drivers we typically encounter with serial link analysis
- Traditional single-step response methods for impulse response generation may not reproduce circuit simulation results accurately enough
- These slides show how an EDA tool can handle this (without changes to the IBIS specification)
- All cases use Micron's y11a.ibs file for 8Gbps DDR5

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## Summary • The **DQ\_34\_3600** I/O model has some asymmetry in its rising and falling edges Standard SerDes step response characterization did not do a great job in capturing this behavior, as seen in the circuit / channel sim correlation • Characterization methods using rising and falling edges captured this behavior very well for channel simulation \*\*\*\*\*\*\*\* [Ramp] R load = 50 typ min max dV/dt r 3.7990E-01/6.4024E-11 3.4860E-01/8.7846E-11 4.0938E-01/4.9359E-11 dV/dt f 4.4605E-01/5.4840E-11 4.6793E-01/4.2557E-11 4.2048E-01/7.6564E-11 cādence























## Summary

- Using default CDR instead of actual strobe to get clock risks will miss important impairments/jitter for parallel bus topology
- Analysis results show false optimism using CDR approach as compared to true strobe timing methodology
- Need to model delay accurately

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